Application No. 09/500,288

GaN substrate with crack prevention and special grow method to reduce compressive strain and thermal relief

Search	L No.	Hits	Text Search		
BRS	Li	270769	(led (light adj emitting adj device))		Data Bases USPAT: EPO; JI
BRS	L2	1152		6/21/01 11:43	Derwent; IBM TI USPAT; EPO; JF
BRS			I and gan	6/21/01 11:43	Derwent; IBM TI
	L3	4	2 and (crack adj prevention)	6/21/01 11:44	USPAT; EPO; JP Derwent; IBM TI
BRS	L4	15	2 and (compressive adj strain)	6/21/01 11:53	USPAT: EPO; JP Derwent; IBM TI
BRS	L2	49	1 and (concave convex)	6/21/01 13:03	USPAT; EPO; JP Derwent; IBM TE
BRS	<u>L7</u>	77	((led (light adj emitting adj device))) and ((gan (gallium adj nitride)) adj substrate)	6/21/01 13:59	USPAT; EPO; JPo Derwent; IBM TD
BRS	L8	30	7 and (single adj crystal)	6/21/01 13:59	USPAT: EPO; JPO
BRS	L9	5 8	3 and compressive adj strain	6/21/01 13:59	Derwent: IBM TD USPAT: EPO: JPO Derwent: IBM TD
				2.27.01 13.57	Derweitt, IBM ID

Search Result

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			Method of growing nitride	Cl/Sub	Cl/Sub	Inventor
1	1 1		semiconductors, nitride semiconductor		1	j
I	1 1		substrate and nitride semiconductor	1	117/10/ 117/050	ļ
US 6153010 A	20001128	35	device	117/95	117/106 ; 117/952	
	ł T		Extended wavelength strained layer	11//93	117/97	Kiyoku, Hiroyuki , et al.
	19981020		lasers having strain compensated		257/17 ; 257/18 ;	
US 5825796 A		32	layers	372/45	257/190 ; 257/94 ; 372/46	•
i				372/43	257/190 ; 257/196	Jewell, Jack L., et al.
l	1	- 1			257/201 : 257/615	
	' I	- 1	Gallium nitride type compound	ł	257/618 : 257/622	
	ł	j	semiconductor light-emitting device	j	257/623 : 257/76 :	• [
	[l)	having buffer layer with non-flat		257/97; 372/45:	
US 6091083 A	20000718		surface	257/79	372/46	17. 77. 11.
116 (0570-0		T	Three-dimensional picture image display	237117	3/2/40	Hata, Toshio, et al.
US 6057878 A	20000502	36[8	apparatus	348/56	348/51	0-:
	ŀ	I	ntegrated optical control element and a	3.0730	346/31	Ogiwara, Akifumi, et al.
1		ſr	nethod for fabricating the same and		1	j
1		ļc	optical integrated circuit element and			
LIC FRANCE .		0	optical integrated circuit device using			
US 5838854 A	19981117		he same	385/50	359/124	Tonovo Marada
US 6707104 A		[S	emiconductor light emitting element		33 % 124	Taneya, Mototaka, et al.
US 5787104 A	19980728	44 a	nd method for fabricating the same	372/43	372/45	Kamiyama Catali
20010002048	j	[3.2.13	Kamiyama, Satoshi, et al.
A1	ì	L	ight-emitting device using group III		ļ	Koike, Masavoshi,
		26 n	itride group compound semiconductor			Yamakazi, Shiro, et al.
[1	180	emiconductor light emitting device with			r amakazi, Shiro , et al.
		ar	active layer made of			
'S 6072197 A	20000.0	se	emiconductor having uniaxial		257/627 : 257/628 :	
3 00/219/ A	20000606	42 an	nisotropy			Horino, Kazuhiko , et al.
'S 5689123 A	1007111	[11]	I-V aresenide-nitride semiconductor		257/18:257/184:	riornio, Kazuniko , et al.
3 2009123 A	19971118	21 m:	aterials and devices	257/190		Major, Jo S., et al.
						major, 10 S., et al.
						
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6/21/01 East Search Data Bases Search L No. Hits Text Search ((led (light adj emitting adj device))) and USPAT; EPO; JPO: BRS L7 (gan (gallium adj nitride)) 6/21/01 14:58 Derwent; IBM TDB USPAT; EPO; JPO: 6/21/01 14:58 Derwent; IBM TDB BRS 292 L8 7 and single adj crystal USPAT; EPO; JPO: Derwent; IBM TDB L9 6/21/01 14:58 BRS 8 and compressive adj strain 8 and (coefficient near (thermal adj USPAT; EPO; JPO: BRS L10 expansion)) 6/21/01 14:59 Derwent: IBM TDB USPAT; EPO; JPO: 6/21/01 15:00 Derwent; IBM TDB BRS 10 and lateral adj growth LH

Search Result						
USPAT	Date	Page	Title	Cl/Sub	Cl/Sub	Inventor
					117/952 ; 257/103 ;	
					257/13; 257/76;	
			Method for forming GaN semiconductor		372/43 ; 372/44 ;	
			single crystal substrate and GaN diode		438/47; 438/481;	
US 6177292 B1	20010123		with the substrate	438/46	438/493	Hong, Chang-Hee, et al.
	_					<u> </u>
				1		1